EXF

Intel - 5SGSMD8N1F45C2LN Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

D	e	t	а	IS

Product Status	Obsolete
Number of LABs/CLBs	262400
Number of Logic Elements/Cells	695000
Total RAM Bits	51200000
Number of I/O	840
Number of Gates	
Voltage - Supply	0.82V ~ 0.88V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1932-BBGA, FCBGA
Supplier Device Package	1932-FBGA, FC (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/intel/5sgsmd8n1f45c2ln

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 5 lists the maximum allowed input overshoot voltage and the duration of the overshoot voltage as a percentage of device lifetime. The maximum allowed overshoot duration is specified as a percentage of high time over the lifetime of the device. A DC signal is equivalent to 100% of the duty cycle. For example, a signal that overshoots to 3.95 V can be at 3.95 V for only ~21% over the lifetime of the device; for a device lifetime of 10 years, the overshoot duration amounts to ~2 years.

		saring transitions		
Symbol	Description	Condition (V)	Overshoot Duration as % @ T _J = 100°C	Unit
		3.8	100	%
		3.85	64	%
		3.9	36	%
		3.95	21	%
Vi (AC)	AC input voltage	4	12	%
		4.05	7	%
		4.1	4	%
		4.15	2	%
		4.2	1	%

Table 5. Maximum Allowed Overshoot During Transitions

Figure 1. Stratix V Device Overshoot Duration



Symbol	Description	Condition	Min ⁽⁴⁾	Тур	Max ⁽⁴⁾	Unit
t _{RAMP}	Power supply ramp time	Standard POR	200 µs	_	100 ms	—
		Fast POR	200 µs		4 ms	

Table 6. Recommended Operating Conditions for Stratix V Devices (Part 2 of 2)

Notes to Table 6:

(1) V_{CCPD} must be 2.5 V when V_{CCI0} is 2.5, 1.8, 1.5, 1.35, 1.25 or 1.2 V. V_{CCPD} must be 3.0 V when V_{CCI0} is 3.0 V.

(2) If you do not use the design security feature in Stratix V devices, connect V_{CCBAT} to a 1.2- to 3.0-V power supply. Stratix V power-on-reset (POR) circuitry monitors V_{CCBAT}. Stratix V devices will not exit POR if V_{CCBAT} stays at logic low.

(3) C2L and I2L can also be run at 0.90 V for legacy boards that were designed for the C2 and I2 speed grades.

(4) The power supply value describes the budget for the DC (static) power supply tolerance and does not include the dynamic tolerance requirements. Refer to the PDN tool for the additional budget for the dynamic tolerance requirements.

Table 7 lists the transceiver power supply recommended operating conditions for Stratix V GX, GS, and GT devices.

Table 7. Recommended Transceiver Power Supply Operating Conditions for Stratix V GX, GS, and GT Devices (Part 1 of 2)

Symbol	Description	Devices	Minimum ⁽⁴⁾	Typical	Maximum ⁽⁴⁾	Unit
V _{CCA GXBL}	Transceiver channel PLL power supply (left		2.85	3.0	3.15	V
(1), (3)	side)	un, us, ui	2.375	2.5	2.625	v
V _{CCA_GXBR}	Transceiver channel PLL power supply (right	CV CS	2.85	3.0	3.15	V
(1), (3)	side)	ux, us	2.375	2.5	2.625	v
V _{CCA_GTBR}	Transceiver channel PLL power supply (right side)	GT	2.85	3.0	3.15	V
	Transceiver hard IP power supply (left side; C1, C2, I2, and I3YY speed grades)	GX, GS, GT	0.87	0.9	0.93	V
V _{CCHIP_L}	Transceiver hard IP power supply (left side; C2L, C3, C4, I2L, I3, I3L, and I4 speed grades)	GX, GS, GT	0.82	0.85	0.88	V
	Transceiver hard IP power supply (right side; C1, C2, I2, and I3YY speed grades)	GX, GS, GT	0.87	0.9	0.93	V
V _{CCHIP_R}	Transceiver hard IP power supply (right side; C2L, C3, C4, I2L, I3, I3L, and I4 speed grades)	GX, GS, GT	0.82	0.85	0.88	V
	Transceiver PCS power supply (left side; C1, C2, I2, and I3YY speed grades)	GX, GS, GT	0.87	0.9	0.93	V
V _{CCHSSI_L}	Transceiver PCS power supply (left side; C2L, C3, C4, I2L, I3, I3L, and I4 speed grades)	GX, GS, GT	0.82	0.85	0.88	V
	Transceiver PCS power supply (right side; C1, C2, I2, and I3YY speed grades)	GX, GS, GT	0.87	0.9	0.93	V
V _{CCHSSI_R}	Transceiver PCS power supply (right side; C2L, C3, C4, I2L, I3, I3L, and I4 speed grades)	GX, GS, GT	0.82	0.85	0.88	V
			0.82	0.85	0.88	
V _{CCR_GXBL}	Receiver analog nower supply (left side)		0.87	0.90	0.93	v
(2) _	Therefore analog power supply (left Slue)	un, uo, ui	0.97	1.0	1.03	V
			1.03	1.05	1.07	

I/O Pin Leakage Current

Table 9 lists the Stratix V I/O pin leakage current specifications.

Table 9.	I/O Pin	Leakage	Current for	Stratix V	Devices (1)
----------	---------	---------	--------------------	-----------	-------------

Symbol	Description	Conditions	Min	Тур	Max	Unit
I _I	Input pin	$V_I = 0 V \text{ to } V_{CCIOMAX}$	-30	_	30	μA
I _{OZ}	Tri-stated I/O pin	$V_0 = 0 V \text{ to } V_{\text{CCIOMAX}}$	-30		30	μA

Note to Table 9:

(1) If $V_0 = V_{CCI0}$ to $V_{CCI0Max}$, 100 μ A of leakage current per I/O is expected.

Bus Hold Specifications

Table 10 lists the Stratix V device family bus hold specifications.

Table 10. Bus Hold Parameters for Stratix V Devices

			V _{CCI0}										
Parameter	Symbol	Conditions	1.2	2 V	1.	5 V	1.8	B V	2.5	5 V	3.0	V	Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Low sustaining current	I _{SUSL}	V _{IN} > V _{IL} (maximum)	22.5	_	25.0	_	30.0	_	50.0	_	70.0	_	μA
High sustaining current	I _{SUSH}	V _{IN} < V _{IH} (minimum)	-22.5		-25.0	_	-30.0	_	-50.0	_	-70.0		μA
Low overdrive current	I _{odl}	$0V < V_{IN} < V_{CCIO}$		120		160		200	_	300		500	μA
High overdrive current	I _{odh}	$0V < V_{IN} < V_{CCIO}$		-120		-160		-200		-300		-500	μΑ
Bus-hold trip point	V _{TRIP}	_	0.45	0.95	0.50	1.00	0.68	1.07	0.70	1.70	0.80	2.00	۷

On-Chip Termination (OCT) Specifications

If you enable OCT calibration, calibration is automatically performed at power-up for I/Os connected to the calibration block. Table 11 lists the Stratix V OCT termination calibration accuracy specifications.

Table 11. OCT Calibration Accuracy Specifications for Stratix V Devices ⁽¹⁾ (Part 1 of 2)

				Calibratio	n Accuracy		
Symbol	Description	Conditions	C1	C2,12	C3,I3, I3YY	C4,14	Unit
25- $Ω$ R _S	Internal series termination with calibration (25- Ω setting)	V _{CCI0} = 3.0, 2.5, 1.8, 1.5, 1.2 V	±15	±15	±15	±15	%

			Re	esistance	Tolerance		
Symbol	Description	Conditions	C1	C2,I2	C3, I3, I3YY	C4, I4	Unit
50-Ω R _S	Internal series termination without calibration (50- Ω setting)	$V_{CCIO} = 1.8$ and 1.5 V	±30	±30	±40	±40	%
50-Ω R _S	Internal series termination without calibration (50- Ω setting)	V _{CCI0} = 1.2 V	±35	±35	±50	±50	%
100-Ω R _D	Internal differential termination (100- Ω setting)	V _{CCPD} = 2.5 V	±25	±25	±25	±25	%

Table 12. OCT Without Calibration Resistance Tolerance Specifications for Stratix V Devices (Part 2 of 2)

Calibration accuracy for the calibrated series and parallel OCTs are applicable at the moment of calibration. When voltage and temperature conditions change after calibration, the tolerance may change.

OCT calibration is automatically performed at power-up for OCT-enabled I/Os. Table 13 lists the OCT variation with temperature and voltage after power-up calibration. Use Table 13 to determine the OCT variation after power-up calibration and Equation 1 to determine the OCT variation without recalibration.

Equation 1. OCT Variation Without Recalibration for Stratix V Devices (1), (2), (3), (4), (5), (6)

$$R_{OCT} \,=\, R_{SCAL} \Big(1 + \langle \frac{dR}{dT} \times \Delta T \rangle \pm \langle \frac{dR}{dV} \times \Delta V \rangle \Big) \label{eq:ROCT}$$

Notes to Equation 1:

- (1) The R_{OCT} value shows the range of OCT resistance with the variation of temperature and V_{CCIO} .
- (2) R_{SCAL} is the OCT resistance value at power-up.
- (3) ΔT is the variation of temperature with respect to the temperature at power-up.
- (4) ΔV is the variation of voltage with respect to the V_{CCIO} at power-up.
- (5) dR/dT is the percentage change of R_{SCAL} with temperature.
- (6) dR/dV is the percentage change of $\mathsf{R}_{\mathsf{SCAL}}$ with voltage.

Table 13 lists the on-chip termination variation after power-up calibration.

Table 13. OCT Variation after Power-Up Calibration for Stratix V Devices (Part 1 of 2)
--

Symbol	Description	V _{CCIO} (V)	Typical	Unit
		3.0	0.0297	
		2.5	0.0344	
dR/dV	recalibration with voltage without	1.8	0.0499	%/mV
		1.5	0.0744	
		1.2	0.1241	

Symbol	Description	V _{CCIO} (V)	Typical	Unit	
dR/dT		3.0	0.189		
	OCT variation with temperature without recalibration	2.5	0.208	%/°C	
		1.8	0.266		
		1.5	0.273		
		1.2	0.317		

Table 13. OCT Variation after Power-Up Calibration for Stratix V Devices (Part 2 of 2)⁽¹⁾

Note to Table 13:

(1) Valid for a V_{CCIO} range of $\pm 5\%$ and a temperature range of 0° to 85°C.

Pin Capacitance

Table 14 lists the Stratix V device family pin capacitance.

Table 14. Pin Capacitance for Stratix V Devices

Symbol	Description	Value	Unit
CIOTB	Input capacitance on the top and bottom I/O pins	6	pF
C _{IOLR}	Input capacitance on the left and right I/O pins	6	рF
C _{OUTFB}	Input capacitance on dual-purpose clock output and feedback pins	6	pF

Hot Socketing

Table 15 lists the hot socketing specifications for Stratix V devices.

Symbol	Description	Maximum
I _{IOPIN (DC)}	DC current per I/O pin	300 μA
I _{IOPIN (AC)}	AC current per I/O pin	8 mA ⁽¹⁾
IXCVR-TX (DC)	DC current per transceiver transmitter pin	100 mA
IXCVR-RX (DC)	DC current per transceiver receiver pin	50 mA

Note to Table 15:

(1) The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, $|I_{10PIN}| = C dv/dt$, in which C is the I/O pin capacitance and dv/dt is the slew rate.

Internal Weak Pull-Up Resistor

Table 16 lists the weak pull-up resistor values for Stratix V devices.

Symbol	Description	V _{CCIO} Conditions (V) ⁽³⁾	Value ⁽⁴⁾	Unit
		3.0 ±5%	25	kΩ
		2.5 ±5%	25	kΩ
	Value of the I/O pin pull-up resistor before	1.8 ±5%	25	kΩ
R _{PU}	and during configuration, as well as user mode if you enable the programmable	1.5 ±5%	25	kΩ
	pull-up resistor option.	1.35 ±5%	25	kΩ
		1.25 ±5%	25	kΩ
		1.2 ±5%	25	kΩ

Table 16. Internal Weak Pull-Up Resistor for Stratix V Devices (1), (2)

Notes to Table 16:

(1) All I/O pins have an option to enable the weak pull-up resistor except the configuration, test, and JTAG pins.

(2) The internal weak pull-down feature is only available for the JTAG TCK pin. The typical value for this internal weak pull-down resistor is approximately 25 k Ω .

- (3) The pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO}.
- (4) These specifications are valid with a $\pm 10\%$ tolerance to cover changes over PVT.

I/O Standard Specifications

Table 17 through Table 22 list the input voltage (V_{IH} and V_{IL}), output voltage (V_{OH} and V_{OL}), and current drive characteristics (I_{OH} and I_{OL}) for various I/O standards supported by Stratix V devices. These tables also show the Stratix V device family I/O standard specifications. The V_{OL} and V_{OH} values are valid at the corresponding I_{OH} and I_{OL}, respectively.

For an explanation of the terms used in Table 17 through Table 22, refer to "Glossary" on page 65. For tolerance calculations across all SSTL and HSTL I/O standards, refer to Altera knowledge base solution rd07262012_486.

I/O	V _{CCIO} (V)		V _{CCIO} (V)		∟ (V)	VIH	V _{IH} (V)		V _{IH} (V)		V _{OH} (V)	I _{OL}	I _{oh}
Standard	Min	Тур	Max	Min	Max	Min	Max	Max	Min	(mA)	(mA)		
LVTTL	2.85	3	3.15	-0.3	0.8	1.7	3.6	0.4	2.4	2	-2		
LVCMOS	2.85	3	3.15	-0.3	0.8	1.7	3.6	0.2	$V_{CCIO} - 0.2$	0.1	-0.1		
2.5 V	2.375	2.5	2.625	-0.3	0.7	1.7	3.6	0.4	2	1	-1		
1.8 V	1.71	1.8	1.89	-0.3	0.35 * V _{CCIO}	0.65 * V _{CCIO}	V _{CCI0} + 0.3	0.45	V _{CCI0} – 0.45	2	-2		
1.5 V	1.425	1.5	1.575	-0.3	0.35 * V _{CCI0}	0.65 * V _{CCI0}	V _{CCI0} + 0.3	0.25 * V _{CCIO}	0.75 * V _{CCIO}	2	-2		
1.2 V	1.14	1.2	1.26	-0.3	0.35 * V _{CCI0}	0.65 * V _{CCI0}	V _{CCI0} + 0.3	0.25 * V _{CCIO}	0.75 * V _{CCIO}	2	-2		

Table 17. Single-Ended I/O Standards for Stratix V Devices

Symbol/ Description	Conditions	Transceiver Speed Grade 1		Transceiver Speed Grade 2			Transceiver Speed Grade 3			Unit	
		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
t _{pll_lock} (16)	_			10			10		_	10	μs

Table 23. Transceiver Specifications for Stratix V GX and GS Devices ⁽¹⁾ (Part 7 of 7)

Notes to Table 23:

(2) The reference clock common mode voltage is equal to the V_{CCR_GXB} power supply level.

(3) This supply must be connected to 1.0 V if the transceiver is configured at a data rate > 6.5 Gbps, and to 1.05 V if configured at a data rate > 10.3 Gbps when DFE is used. For data rates up to 6.5 Gbps, you can connect this supply to 0.85 V.

- (4) This supply follows VCCR_GXB.
- (5) The device cannot tolerate prolonged operation at this absolute maximum.
- (6) The differential eye opening specification at the receiver input pins assumes that **Receiver Equalization** is disabled. If you enable **Receiver Equalization**, the receiver circuitry can tolerate a lower minimum eye opening, depending on the equalization level.
- (7) The Quartus II software automatically selects the appropriate slew rate depending on the configured data rate or functional mode.
- (8) The input reference clock frequency options depend on the data rate and the device speed grade.
- (9) The line data rate may be limited by PCS-FPGA interface speed grade.
- (10) Refer to Figure 1 for the GX channel AC gain curves. The total effective AC gain is the AC gain minus the DC gain.
- (11) t_{LTR} is the time required for the receive CDR to lock to the input reference clock frequency after coming out of reset.
- (12) t_{LTD} is time required for the receiver CDR to start recovering valid data after the rx_is_lockedtodata signal goes high.
- (13) t_{LTD_manual} is the time required for the receiver CDR to start recovering valid data after the rx_is_lockedtodata signal goes high when the CDR is functioning in the manual mode.
- (14) $t_{LTR_LTD_manual}$ is the time the receiver CDR must be kept in lock to reference (LTR) mode after the rx_is_lockedtoref signal goes high when the CDR is functioning in the manual mode.
- (15) $t_{pll_powerdown}$ is the PLL powerdown minimum pulse width.
- (16) t_{pll lock} is the time required for the transmitter CMU/ATX PLL to lock to the input reference clock frequency after coming out of reset.
- (17) To calculate the REFCLK rms phase jitter requirement for PCIe at reference clock frequencies other than 100 MHz, use the following formula: REFCLK rms phase jitter at f(MHz) = REFCLK rms phase jitter at 100 MHz × 100/f.
- (18) The maximum peak to peak differential input voltage V_{ID} after device configuration is equal to 4 × (absolute V_{MAX} for receiver pin V_{ICM}).
- (19) For ES devices, R_{BEF} is 2000 $\Omega \pm 1\%$.
- (20) To calculate the REFCLK phase noise requirement at frequencies other than 622 MHz, use the following formula: REFCLK phase noise at f(MHz) = REFCLK phase noise at 622 MHz + 20*log(f/622).
- (21) SFP/+ optical modules require the host interface to have RD+/- differentially terminated with 100 Ω. The internal OCT feature is available after the Stratix V FPGA configuration is completed. Altera recommends that FPGA configuration is completed before inserting the optical module. Otherwise, minimize unnecessary removal and insertion with unconfigured devices.
- (22) Refer to Figure 2.
- (23) For oversampling designs to support data rates less than the minimum specification, the CDR needs to be in LTR mode only.
- (24) I3YY devices can achieve data rates up to 10.3125 Gbps.
- (25) When you use fPLL as a TXPLL of the transceiver.
- (26) REFCLK performance requires to meet transmitter REFCLK phase noise specification.
- (27) Minimum eye opening of 85 mV is only for the unstressed input eye condition.

⁽¹⁾ Speed grades shown in Table 23 refer to the PMA Speed Grade in the device ordering code. The maximum data rate could be restricted by the Core/PCS speed grade. Contact your Altera Sales Representative for the maximum data rate specifications in each speed grade combination offered. For more information about device ordering codes, refer to the Stratix V Device Overview.

Symbol/	Conditions	Transceiver Speed Grade 2			S	Unit		
Description		Min	Тур	Max	Min	Тур	Max	
Differential on-chip termination resistors ⁽⁷⁾	GT channels		100	_	_	100	_	Ω
	85- Ω setting	_	85 ± 30%	_	_	85 ± 30%	_	Ω
Differential on-chip	100-Ω setting	_	100 ± 30%	_	_	100 ± 30%	_	Ω
for GX channels ⁽¹⁹⁾	120-Ω setting	_	120 ± 30%	_	—	120 ± 30%	—	Ω
	150-Ω setting		150 ± 30%	_	_	150 ± 30%	_	Ω
V _{ICM} (AC coupled)	GT channels	_	650	_	—	650	—	mV
	VCCR_GXB = 0.85 V or 0.9 V	_	600	_	_	600	_	mV
VICM (AC and DC coupled) for GX Channels	VCCR_GXB = 1.0 V full bandwidth	_	700		_	700	_	mV
	VCCR_GXB = 1.0 V half bandwidth	_	750	_	_	750	_	mV
t _{LTR} ⁽⁹⁾	—	_	—	10	—	—	10	μs
t _{LTD} ⁽¹⁰⁾		4			4	_	_	μs
t _{LTD_manual} ⁽¹¹⁾		4	_		4	_	_	μs
t _{LTR_LTD_manual} ⁽¹²⁾	—	15	—	_	15	—	—	μs
Run Lenath	GT channels		—	72	—	—	72	CID
	GX channels				(8)			
CDR PPM	GT channels	_	—	1000	—	—	1000	± PPM
	GX channels				(8)			
Programmable	GT channels	_		14		_	14	dB
(AC Gain) ⁽⁵⁾	GX channels				(8)			
Programmable	GT channels	_		7.5	_		7.5	dB
DC gain ⁽⁶⁾	GX channels				(8)			
Differential on-chip termination resistors ⁽⁷⁾	GT channels	_	100	—	_	100	_	Ω
Transmitter								
Supported I/O Standards	_	1.4-V and 1.5-V PCML						
Data rate (Standard PCS)	GX channels	600	_	8500	600		8500	Mbps
Data rate (10G PCS)	GX channels	600		12,500	600		12,500	Mbps

Table 28. Transceiver Specifications for Stratix V GT Devices (Part 3 of 5)⁽¹⁾

Table 28. Tra	nsceiver Specifi	cations for Stra	tix V GT Devices	(Part 5 of 5) ⁽¹⁾
---------------	------------------	------------------	------------------	------------------------------

Symbol/ Description	Conditions	Transceiver Speed Grade 2			ן Sr	Unit		
Description		Min	Тур	Max	Min	Тур	Max	
t _{pll_lock} ⁽¹⁴⁾	—	—	_	10	—	—	10	μs

Notes to Table 28:

- (1) Speed grades shown refer to the PMA Speed Grade in the device ordering code. The maximum data rate could be restricted by the Core/PCS speed grade. Contact your Altera Sales Representative for the maximum data rate specifications in each speed grade combination offered. For more information about device ordering codes, refer to the Stratix V Device Overview.
- (2) The reference clock common mode voltage is equal to the VCCR_GXB power supply level.
- (3) The device cannot tolerate prolonged operation at this absolute maximum.
- (4) The differential eye opening specification at the receiver input pins assumes that receiver equalization is disabled. If you enable receiver equalization, the receiver circuitry can tolerate a lower minimum eye opening, depending on the equalization level.
- (5) Refer to Figure 5 for the GT channel AC gain curves. The total effective AC gain is the AC gain minus the DC gain.
- (6) Refer to Figure 6 for the GT channel DC gain curves.
- (7) CFP2 optical modules require the host interface to have the receiver data pins differentially terminated with 100 Ω. The internal OCT feature is available after the Stratix V FPGA configuration is completed. Altera recommends that FPGA configuration is completed before inserting the optical module. Otherwise, minimize unnecessary removal and insertion with unconfigured devices.
- (8) Specifications for this parameter are the same as for Stratix V GX and GS devices. See Table 23 for specifications.
- (9) t_{1 TR} is the time required for the receive CDR to lock to the input reference clock frequency after coming out of reset.
- (10) t_{LTD} is time required for the receiver CDR to start recovering valid data after the rx is lockedtodata signal goes high.
- (11) t_{LTD_manual} is the time required for the receiver CDR to start recovering valid data after the rx_is_lockedtodata signal goes high when the CDR is functioning in the manual mode.
- (12) t_{LTR_LTD_manual} is the time the receiver CDR must be kept in lock to reference (LTR) mode after the rx_is_lockedtoref signal goes high when the CDR is functioning in the manual mode.
- (13) tpll_powerdown is the PLL powerdown minimum pulse width.
- (14) tpll lock is the time required for the transmitter CMU/ATX PLL to lock to the input reference clock frequency after coming out of reset.
- (15) To calculate the REFCLK rms phase jitter requirement for PCle at reference clock frequencies other than 100 MHz, use the following formula: REFCLK rms phase jitter at f(MHz) = REFCLK rms phase jitter at 100 MHz × 100/f.
- (16) The maximum peak to peak differential input voltage V_{ID} after device configuration is equal to 4 × (absolute V_{MAX} for receiver pin V_{ICM}).
- (17) For ES devices, RREF is 2000 $\Omega \pm 1\%$.
- (18) To calculate the REFCLK phase noise requirement at frequencies other than 622 MHz, use the following formula: REFCLK phase noise at f(MHz) = REFCLK phase noise at 622 MHz + 20*log(f/622).
- (19) SFP/+ optical modules require the host interface to have RD+/- differentially terminated with 100 Ω. The internal OCT feature is available after the Stratix V FPGA configuration is completed. Altera recommends that FPGA configuration is completed before inserting the optical module. Otherwise, minimize unnecessary removal and insertion with unconfigured devices.
- (20) Refer to Figure 4.
- (21) For oversampling design to support data rates less than the minimum specification, the CDR needs to be in LTR mode only.
- (22) This supply follows VCCR_GXB for both GX and GT channels.
- (23) When you use fPLL as a TXPLL of the transceiver.

Table 29 shows the V_{OD} settings for the GT channel.

Symbol	V _{OD} Setting	V _{od} Value (mV)
	0	0
	1	200
V., differential neak to neak typical (1)	2	400
The american hear to hear thicat to	3	600
	4	800
	5	1000

Note:

(1) Refer to Figure 4.

PLL Specifications

Table 31 lists the Stratix V PLL specifications when operating in both the commercial junction temperature range (0° to 85° C) and the industrial junction temperature range (-40° to 100° C).

Table 31. PLL Specifications for Stratix V Devices (Part 1 of 3)

Symbol	Parameter	Min	Тур	Max	Unit
	Input clock frequency (C1, C2, C2L, I2, and I2L speed grades)	5		800 (1)	MHz
f _{IN}	Input clock frequency (C3, I3, I3L, and I3YY speed grades)	5		800 (1)	MHz
	Input clock frequency (C4, I4 speed grades)	5	—	650 ⁽¹⁾	MHz
f _{INPFD}	Input frequency to the PFD	5	—	325	MHz
f _{FINPFD}	Fractional Input clock frequency to the PFD	50	—	160	MHz
	PLL VCO operating range (C1, C2, C2L, I2, I2L speed grades)	600	_	1600	MHz
f _{VCO} (9)	PLL VCO operating range (C3, I3, I3L, I3YY speed grades)	600		1600	MHz
	PLL VCO operating range (C4, I4 speed grades)	600	—	1300	MHz
t _{einduty}	Input clock or external feedback clock input duty cycle	40	—	60	%
	Output frequency for an internal global or regional clock (C1, C2, C2L, I2, I2L speed grades)	_	_	717 ⁽²⁾	MHz
f _{out}	Output frequency for an internal global or regional clock (C3, I3, I3L speed grades)			650 ⁽²⁾	MHz
	Output frequency for an internal global or regional clock (C4, I4 speed grades)			580 ⁽²⁾	MHz
	Output frequency for an external clock output (C1, C2, C2L, I2, I2L speed grades)			800 ⁽²⁾	MHz
f _{OUT_EXT}	Output frequency for an external clock output (C3, I3, I3L speed grades)			667 ⁽²⁾	MHz
	Output frequency for an external clock output (C4, I4 speed grades)			553 ⁽²⁾	MHz
t _{outduty}	Duty cycle for a dedicated external clock output (when set to 50%)	45	50	55	%
t _{FCOMP}	External feedback clock compensation time	_		10	ns
f _{dyconfigclk}	Dynamic Configuration Clock used for mgmt_clk and scanclk		_	100	MHz
t _{LOCK}	Time required to lock from the end-of-device configuration or deassertion of areset			1	ms
t _{DLOCK}	Time required to lock dynamically (after switchover or reconfiguring any non-post-scale counters/delays)			1	ms
	PLL closed-loop low bandwidth	—	0.3	—	MHz
f _{CLBW}	PLL closed-loop medium bandwidth	—	1.5	—	MHz
	PLL closed-loop high bandwidth (7)	—	4	-	MHz
t _{PLL_PSERR}	Accuracy of PLL phase shift	—	—	±50	ps
t _{ARESET}	Minimum pulse width on the areset signal	10	—	_	ns

		Resources Used				Ρε	erforman	ce			
Memory	Mode	ALUTS	Memory	C1	C2, C2L	C3	C4	12, 12L	13, 13L, 13YY	14	Unit
	Single-port, all supported widths	0	1	700	700	650	550	700	500	450	MHz
	Simple dual-port, all supported widths	0	1	700	700	650	550	700	500	450	MHz
	Simple dual-port with the read-during-write option set to Old Data , all supported widths	0	1	525	525	455	400	525	455	400	MHz
M20K Block	Simple dual-port with ECC enabled, 512 × 32	0	1	450	450	400	350	450	400	350	MHz
	Simple dual-port with ECC and optional pipeline registers enabled, 512 × 32	0	1	600	600	500	450	600	500	450	MHz
	True dual port, all supported widths	0	1	700	700	650	550	700	500	450	MHz
	ROM, all supported widths	0	1	700	700	650	550	700	500	450	MHz

Table 33. Memory Block Performance Specifications for Stratix V Devices ^{(1), (2)} (Part 2 of 2)

Notes to Table 33:

(1) To achieve the maximum memory block performance, use a memory block clock that comes through global clock routing from an on-chip PLL set to **50**% output duty cycle. Use the Quartus II software to report timing for this and other memory block clocking schemes.

(2) When you use the error detection cyclical redundancy check (CRC) feature, there is no degradation in F_{MAX}.

(3) The F_{MAX} specification is only achievable with Fitter options, MLAB Implementation In 16-Bit Deep Mode enabled.

Temperature Sensing Diode Specifications

Table 34 lists the internal TSD specification.

Table 34. Internal Temperature Sensing Diode Specification

Temperature Range	Accuracy	Offset Calibrated Option	Offset Calibrated Option No 1 MHz, 500 KHz		Resolution	Minimum Resolution with no Missing Codes
-40°C to 100°C	±8°C	No	1 MHz, 500 KHz	< 100 ms	8 bits	8 bits

Table 35 lists the specifications for the Stratix V external temperature sensing diode.

Table 35.	External	Temperature	Sensing Dic	de Specifica	ations for Stratix	V Devices
-----------	----------	-------------	-------------	--------------	--------------------	-----------

Description	Min	Тур	Max	Unit
I _{bias} , diode source current	8	—	200	μA
V _{bias,} voltage across diode	0.3	—	0.9	V
Series resistance	—	_	< 1	Ω
Diode ideality factor	1.006	1.008	1.010	_

Figure 7 shows the dynamic phase alignment (DPA) lock time specifications with the DPA PLL calibration option enabled.

Figure 7. DPA Lock Time Specification with DPA PLL Calibration Enabled

rx_reset			
rx_dpa_locked			<u> </u>
			-

Table 37 lists the DPA lock time specifications for Stratix V devices.

Table 37. DPA Lock Time Specifications for Stratix V GX Devices Only (1), (2), (3)

Standard	Training Pattern	Number of Data Transitions in One Repetition of the Training Pattern	Number of Repetitions per 256 Data Transitions ⁽⁴⁾	Maximum
SPI-4	00000000001111111111	2	128	640 data transitions
Parallel Rapid I/O	00001111	2	128	640 data transitions
	10010000	4	64	640 data transitions
Miscellaneous	10101010	8	32	640 data transitions
Wiscenareous	01010101	8	32	640 data transitions

Notes to Table 37:

(1) The DPA lock time is for one channel.

(2) One data transition is defined as a 0-to-1 or 1-to-0 transition.

(3) The DPA lock time stated in this table applies to both commercial and industrial grade.

(4) This is the number of repetitions for the stated training pattern to achieve the 256 data transitions.

Figure 8 shows the **LVDS** soft-clock data recovery (CDR)/DPA sinusoidal jitter tolerance specification for a data rate \geq 1.25 Gbps. Table 38 lists the **LVDS** soft-CDR/DPA sinusoidal jitter tolerance specification for a data rate \geq 1.25 Gbps.





Speed Grade	Min	Max	Unit	
C4,I4	8	16	ps	

Table 40. DQS Phase Offset Delay Per Setting for Stratix V Devices ^{(1), (2)} (Part 2 of 2)

Notes to Table 40:

(1) The typical value equals the average of the minimum and maximum values.

(2) The delay settings are linear with a cumulative delay variation of 40 ps for all speed grades. For example, when using a -2 speed grade and applying a 10-phase offset setting to a 90° phase shift at 400 MHz, the expected average cumulative delay is [625 ps + (10 × 10 ps) ± 20 ps] = 725 ps ± 20 ps.

Table 41 lists the DQS phase shift error for Stratix V devices.

Table 41. DQS Phase Shift Error Specification for DLL-Delayed Clock (t_{DQS_PSERR}) for Stratix V Devices ⁽¹⁾

Number of DQS Delay Buffers	C1	C2, C2L, I2, I2L	C3, I3, I3L, I3YY	C4,14	Unit
1	28	28	30	32	ps
2	56	56	60	64	ps
3	84	84	90	96	ps
4	112	112	120	128	ps

Notes to Table 41:

(1) This error specification is the absolute maximum and minimum error. For example, skew on three DQS delay buffers in a -2 speed grade is ± 78 ps or ± 39 ps.

Table 42 lists the memory output clock jitter specifications for Stratix V devices.

Table 42. Memory Output Clock Jitter Specification for Stratix V Devices (1	^{),} (Part 1 of 2) ^{(2), (3)}
---	---

Clock Network	Parameter	Symbol	C1		C2, C2L, I2, I2L		C3, I3, I3L, I3YY		C4,14		Unit
NELWURK		-	Min	Max	Min	Max	Min	Max	Min	Max	
	Clock period jitter	$t_{JIT(per)}$	-50	50	-50	50	-55	55	-55	55	ps
Regional	Cycle-to-cycle period jitter	$t_{\text{JIT(cc)}}$	-100	100	-100	100	-110	110	-110	110	ps
	Duty cycle jitter	$t_{JIT(duty)}$	-50	50	-50	50	-82.5	82.5	-82.5	82.5	ps
	Clock period jitter	$t_{JIT(per)}$	-75	75	-75	75	-82.5	82.5	-82.5	82.5	ps
Global	Cycle-to-cycle period jitter	$t_{\text{JIT(cc)}}$	-150	150	-150	150	-165	165	-165	165	ps
	Duty cycle jitter	$t_{JIT(duty)}$	-75	75	-75	75	-90	90	-90	90	ps

Duty Cycle Distortion (DCD) Specifications

Table 44 lists the worst-case DCD for Stratix V devices.

Table 44. Worst-Case DCD on Stratix V I/O Pins (1)

Symbol	C	1	C2, C2	C2, C2L, I2, I2L		C3, I3, I3L, I3YY		4,14	Unit	
-	Min	Max	Min	Max	Min	Max	Min	Max		
Output Duty Cycle	45	55	45	55	45	55	45	55	%	

Note to Table 44:

(1) The DCD numbers do not cover the core clock network.

Configuration Specification

POR Delay Specification

Power-on reset (POR) delay is defined as the delay between the time when all the power supplies monitored by the POR circuitry reach the minimum recommended operating voltage to the time when the nSTATUS is released high and your device is ready to begin configuration.



For more information about the POR delay, refer to the *Hot Socketing and Power-On Reset in Stratix V Devices* chapter.

Table 45 lists the fast and standard POR delay specification.

Table 45. Fast and Standard POR Delay Specification (1)

POR Delay	Minimum	Maximum
Fast	4 ms	12 ms
Standard	100 ms	300 ms

Note to Table 45:

(1) You can select the POR delay based on the MSEL settings as described in the MSEL Pin Settings section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices" chapter.

JTAG Configuration Specifications

Table 46 lists the JTAG timing parameters and values for Stratix V devices.

Table 46. JTAG Timing Parameters and Values for Stratix V Devices

Symbol	Description	Min	Max	Unit
t _{JCP}	TCK clock period ⁽²⁾	30		ns
t _{JCP}	TCK clock period ⁽²⁾	167	—	ns
t _{JCH}	TCK clock high time ⁽²⁾	14	—	ns
t _{JCL}	TCK clock low time ⁽²⁾	14		ns
t _{JPSU (TDI)}	TDI JTAG port setup time	2	—	ns
t _{JPSU (TMS)}	TMS JTAG port setup time	3	_	ns

Symbol	Description	Min	Max	Unit
t _{JPH}	JTAG port hold time	5	—	ns
t _{JPCO}	JTAG port clock to output	—	11 ⁽¹⁾	ns
t _{JPZX}	JTAG port high impedance to valid output	—	14 ⁽¹⁾	ns
t _{JPXZ}	JTAG port valid output to high impedance	—	14 ⁽¹⁾	ns

Table 46. JTAG Timing Parameters and Values for Stratix V Devices

Notes to Table 46:

(1) A 1 ns adder is required for each V_{CCI0} voltage step down from 3.0 V. For example, $t_{JPC0} = 12$ ns if V_{CCI0} of the TDO I/O bank = 2.5 V, or 13 ns if it equals 1.8 V.

(2) The minimum TCK clock period is 167 ns if VCCBAT is within the range 1.2V-1.5V when you perform the volatile key programming.

Raw Binary File Size

For the POR delay specification, refer to the "POR Delay Specification" section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices".

Table 47 lists the uncompressed raw binary file (.rbf) sizes for Stratix V devices.

Family	Device	Package	Configuration .rbf Size (bits)	IOCSR .rbf Size (bits) ^{(4), (5)}
	500742	H35, F40, F35 ⁽²⁾	213,798,880	562,392
	JOUNAS	H29, F35 ⁽³⁾	137,598,880	564,504
	5SGXA4	—	213,798,880	563,672
	5SGXA5	—	269,979,008	562,392
	5SGXA7	—	269,979,008	562,392
Stratix V GX	5SGXA9	—	342,742,976	700,888
	5SGXAB	—	342,742,976	700,888
	5SGXB5	—	270,528,640	584,344
	5SGXB6	—	270,528,640	584,344
	5SGXB9	_	342,742,976	700,888
	5SGXBB	—	342,742,976	700,888
Stratix V GT	5SGTC5	—	269,979,008	562,392
	5SGTC7	_	269,979,008	562,392
	5SGSD3	—	137,598,880	564,504
Ctratic V CC	500004	F1517	213,798,880	563,672
	J303D4		137,598,880	564,504
	5SGSD5	—	213,798,880	563,672
	5SGSD6		293,441,888	565,528
	5SGSD8	—	293,441,888	565,528

Table 47. Uncompressed .rbf Sizes for Stratix V Devices

Active Serial Configuration Timing

Table 52 lists the DCLK frequency specification in the AS configuration scheme.

Fable 52.	DCLK Frequency	Specification in th	e AS Configuration	Scheme ^{(1),}	(2)
-----------	----------------	---------------------	--------------------	------------------------	-----

Minimum	Typical	Maximum	Unit
5.3	7.9	12.5	MHz
10.6	15.7	25.0	MHz
21.3	31.4	50.0	MHz
42.6	62.9	100.0	MHz

Notes to Table 52:

(1) This applies to the DCLK frequency specification when using the internal oscillator as the configuration clock source.

(2) The AS multi-device configuration scheme does not support DCLK frequency of 100 MHz.

Figure 14 shows the single-device configuration setup for an AS ×1 mode.





Notes to Figure 14:

- (1) If you are using AS $\times 4$ mode, this signal represents the AS_DATA[3..0] and EPCQ sends in 4-bits of data for each DCLK cycle.
- (2) The initialization clock can be from internal oscillator or CLKUSR pin.
- (3) After the option bit to enable the INIT_DONE pin is configured into the device, the INIT_DONE goes low.

Table 53 lists the timing parameters for AS $\times 1$ and AS $\times 4$ configurations in Stratix V devices.

Table JS. As fining falancees for as $\times 1$ and as $\times 4$ configurations in straits V devices $(2, 2, 2, 3, 3, 3, 3, 3, 3, 3, 3, 3, 3, 3, 3, 3,$	Table 53.	AS Timing	Parameters for AS	\times 1 and AS \times 4 Confi	gurations in Stratix V	/ Devices ^{(1),} (2)	(Part 1 of 2)
--	-----------	-----------	--------------------------	------------------------------------	------------------------	-------------------------------	---------------

Symbol	Parameter	Minimum	Maximum	Units
t _{CO}	DCLK falling edge to AS_DATA0/ASDO output	—	2	ns
t _{SU}	Data setup time before falling edge on DCLK	1.5	_	ns
t _H	Data hold time after falling edge on DCLK	0	_	ns

Letter	Subject	Definitions		
	V _{CM(DC)}	DC common mode input voltage.		
	V _{ICM}	Input common mode voltage—The common mode of the differential signal at the receiver.		
	V _{ID}	Input differential voltage swing—The difference in voltage between the positive and complementary conductors of a differential transmission at the receiver.		
	V _{DIF(AC)}	AC differential input voltage—Minimum AC input differential voltage required for switching.		
	V _{DIF(DC)}	DC differential input voltage— Minimum DC input differential voltage required for switching.		
	V _{IH}	Voltage input high—The minimum positive voltage applied to the input which is accepted by the device as a logic high.		
	V _{IH(AC)}	High-level AC input voltage		
	V _{IH(DC)}	High-level DC input voltage		
V	V _{IL}	Voltage input low—The maximum positive voltage applied to the input which is accepted by the device as a logic low.		
	V _{IL(AC)}	Low-level AC input voltage		
	V _{IL(DC)}	Low-level DC input voltage		
	V _{OCM}	Output common mode voltage—The common mode of the differential signal at the transmitter.		
	V _{OD}	Output differential voltage swing—The difference in voltage between the positive and complementary conductors of a differential transmission at the transmitter.		
	V _{SWING}	Differential input voltage		
	V _X	Input differential cross point voltage		
	V _{OX}	Output differential cross point voltage		
W	W	High-speed I/O block—clock boost factor		
X				
Y	—	—		
Z				

Table 60. Glossary (Part 4 of 4)

Document Revision History

Table 61 lists the revision history for this chapter.

 Table 61. Document Revision History (Part 1 of 3)

Date	Version	Changes		
June 2018	3.9	 Added the "Stratix V Device Overshoot Duration" figure. 		
		Added a footnote to the "High-Speed I/O Specifications for Stratix V Devices" table.		
April 2017		 Changed the minimum value for t_{CD2UMC} in the "PS Timing Parameters for Stratix V Devices" table. 		
		 Changed the condition for 100-Ω R_D in the "OCT Without Calibration Resistance Tolerance Specifications for Stratix V Devices" table. 		
	3.8	 Changed the minimum value for t_{CD2UMC} in the "AS Timing Parameters for AS '1 and AS '4 Configurations in Stratix V Devices" table 		
		 Changed the minimum value for t_{CD2UMC} in the "FPP Timing Parameters for Stratix V Devices When the DCLK-to-DATA[] Ratio is >1" table. 		
		 Changed the minimum value for t_{CD2UMC} in the "FPP Timing Parameters for Stratix V Devices When the DCLK-to-DATA[] Ratio is >1" table. 		
		 Changed the minimum number of clock cycles value in the "Initialization Clock Source Option and the Maximum Frequency" table. 		
lune 0010	3.7	 Added the V_{ID} minimum specification for LVPECL in the "Differential I/O Standard Specifications for Stratix V Devices" table 		
Julie 2010		 Added the I_{OUT} specification to the "Absolute Maximum Ratings for Stratix V Devices" table. 		
December 2015	3.6	Added a footnote to the "High-Speed I/O Specifications for Stratix V Devices" table.		
D 1 0015	3.5	 Changed the transmitter, receiver, and ATX PLL data rate specifications in the "Transceiver Specifications for Stratix V GX and GS Devices" table. 		
		 Changed the configuration .rbf sizes in the "Uncompressed .rbf Sizes for Stratix V Devices" table. 		
		• Changed the data rate specification for transceiver speed grade 3 in the following tables:		
		 "Transceiver Specifications for Stratix V GX and GS Devices" 		
		 "Stratix V Standard PCS Approximate Maximum Date Rate" 		
		 "Stratix V 10G PCS Approximate Maximum Data Rate" 		
July 2015	3.4	 Changed the conditions for reference clock rise and fall time, and added a note to the "Transceiver Specifications for Stratix V GX and GS Devices" table. 		
		 Added a note to the "Minimum differential eye opening at receiver serial input pins" specification in the "Transceiver Specifications for Stratix V GX and GS Devices" table. 		
		 Changed the t_{c0} maximum value in the "AS Timing Parameters for AS '1 and AS '4 Configurations in Stratix V Devices" table. 		
		 Removed the CDR ppm tolerance specification from the "Transceiver Specifications for Stratix V GX and GS Devices" table. 		

Table 61. Document Revision History (Part 2 of 3)

Date	Version	Changes
		 Added the I3YY speed grade and changed the data rates for the GX channel in Table 1.
		 Added the I3YY speed grade to the V_{CC} description in Table 6.
		 Added the I3YY speed grade to V_{CCHIP_L}, V_{CCHIP_R}, V_{CCHSSI_L}, and V_{CCHSSI_R} descriptions in Table 7.
		■ Added 240-Ω to Table 11.
		Changed CDR PPM tolerance in Table 23.
		 Added additional max data rate for fPLL in Table 23.
		 Added the I3YY speed grade and changed the data rates for transceiver speed grade 3 in Table 25.
		 Added the I3YY speed grade and changed the data rates for transceiver speed grade 3 in Table 26.
		 Changed CDR PPM tolerance in Table 28.
		 Added additional max data rate for fPLL in Table 28.
		 Changed the mode descriptions for MLAB and M20K in Table 33.
		 Changed the Max value of f_{HSCLK_OUT} for the C2, C2L, I2, I2L speed grades in Table 36.
November 2014	3.3	 Changed the frequency ranges for C1 and C2 in Table 39.
		 Changed the .rbf file sizes for 5SGSD6 and 5SGSD8 in Table 47.
		 Added note about nSTATUS to Table 50, Table 51, Table 54.
		 Changed the available settings in Table 58.
		 Changed the note in "Periphery Performance".
		 Updated the "I/O Standard Specifications" section.
		 Updated the "Raw Binary File Size" section.
		 Updated the receiver voltage input range in Table 22.
		 Updated the max frequency for the LVDS clock network in Table 36.
		■ Updated the DCLK note to Figure 11.
		 Updated Table 23 VO_{CM} (DC Coupled) condition.
		Updated Table 6 and Table 7.
		 Added the DCLK specification to Table 55.
		Updated the notes for Table 47.
		 Updated the list of parameters for Table 56.
November 2013	3.2	Updated Table 28
November 2013	3.1	Updated Table 33
November 2013	3.0	Updated Table 23 and Table 28
October 2013	2.9	 Updated the "Transceiver Characterization" section
		 Updated Table 3, Table 12, Table 14, Table 19, Table 20, Table 23, Table 24, Table 28, Table 30, Table 31, Table 32, Table 33, Table 36, Table 39, Table 40, Table 41, Table 42, Table 47, Table 53, Table 58, and Table 59
Uctober 2013	2.8	 Added Figure 1 and Figure 3
		 Added the "Transceiver Characterization" section
		 Removed all "Preliminary" designations.